



SHEET 1 OF 1

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMEX.367AAPPLICATION NO.
10/074,534INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Michael A. ToddFILING DATE
February 11, 2002GROUP
2814

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	Todd, Michael A. et al., "Deposition of Si _{1-x} Ge _x Films for Gate Electrode Applications Using a Novel Approach," ICSI3, The SiGe Conference; Santa Fe, NM, March 2003

S:\DOCS\JOM\JOM-5285.DOC:092603

EXAMINER 	DATE CONSIDERED 3/4/04
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	



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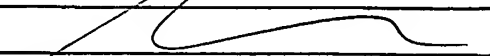
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1.	5,389,398	02/14/95	Suzuki et al.	427	130	
	2.	5,698,771	12/16/97	Shields et al.	73	31.05	
	3.	6,228,181	05/08/01	Yamamoto et al.	148	33.5	
	4.	6,326,311	12/04/01	Ueda et al.	438	694	
	5.	6,455,892	09/24/02	Okuno et al.	257	328	
	6.	6,613,695	09/02/03	Pomarede et al.	438	767	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	7.	Ikoma et al., Growth of Si/3C-SiC/Si(100) heterostructures by pulsed supersonic free jets, Applied Physics Letters, Volume 75, No. 25, Pp. 3977-3979, December 1999

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